



UNIVERSITY OF RUHUNA

Faculty of Engineering

End-Semester 5 Examination in Engineering: July 2016

Module Number: EE5305

Module Name: Sensors, Transducers and
Measurement Techniques

[Three Hours]

[Answer all questions, each question carries 10 marks]

- Q1 a) i) Sketch the typical Energy (E) versus quantum mechanical wave number (k) diagrams for a direct and an indirect gap semiconductor.
- ii) Describe the reason for the probability of band to band transition in a direct gap semiconductor being much greater than that of an indirect gap semiconductor.
- iii) Describe the three band to band transitions in a direct gap semiconductor with the aid of diagrams.
- [3.5 Marks]
- b) The absorption and gain coefficients of a LASER are $\alpha(\nu)$ and $g(\nu)$ respectively, where ν represent frequency. The valence and conduction bands are denoted by E_1 and E_2 respectively. The probability of electron transition from the valence band to the conduction band is $f_V(E_1)$ and from conduction to the valence band is $f_C(E_2)$.
- i) Express $\alpha(\nu)$ and $g(\nu)$ in terms of $f_V(E_1)$ and $f_C(E_2)$ taking the proportionality constant as α_0 .
- ii) State the relation between $\alpha(\nu)$ and $g(\nu)$ for charge carriers in equilibrium.
- iii) Explain the conditions necessary for population inversion for a LASER.
- [3 Marks]
- c) i) Describe the active region in a LED homojunction.
- ii) Sketch the energy band diagram, carrier concentration, refractive index profile and the optical field of a p-n homojunction of a LED.
- iii) Sketch the energy band diagram, carrier concentration, refractive index profile and the optical field of the semiconductor structure for a double heterostructure of a LASER.
- [3.5 Marks]
- Q2 a) i) Sketch the basic structure of a LED and label the component parts.
- ii) I. Sketch the typical Light current (L - I) characteristic of a LED and its frequency response.
- II. Identify the linear response region of the characteristic and explain how direct current modulation can be achieved in this region.

- iii) The output optical power of the LED in response to input current modulation can be expressed as

$$P(t) = P_0 + P_1(t) = P_0 [1 + |r| \cos(\Omega t - \phi)]$$

I. Explain the different terms in the equation.

II. State the semiconductor parameter that determines the maximum modulation speed of a LED.

[5 Marks]

- b) i) State the general conditions for a LASER to oscillate at a particular frequency.
 ii) Name the corresponding condition in Electronics.
 iii) Describe the reason for having a resonant cavity for optical feedback in a LASER.
 iv) Sketch the structures of an edge emitting and a surface emitting LASER based on Bragg reflectors.
 v) Explain the reason for the high modulation speed of a LASER as compared to a LED.

[5 Marks]

- Q3 a) i) State and explain the origin of the two fundamental noise phenomena in a photodetector.
 ii) Define the noise s_n of a signal s .
 iii) State two important characteristics of the noise s_n and their significance in signal processing.

[2 Marks]

- b) i) Show that the photocurrent i_s in a photodetector that has unity gain and no noise is given by

$$i_s = \eta_e e P_s / h\nu$$

where η_e is quantum efficiency, e is the electron charge, P_s the input optical power and $h\nu$ the photon energy respectively.

- ii) If the mean square noise in the incident photon number S and the generated charge carriers N are given by their mean values show that the expression for the shot noise of the photodetector is given by

$$\overline{i_{n,sh}^2} = 2\eta_e e^2 B \overline{P_s} / h\nu$$

where the bar indicates mean values.

Hint: Use the expressions derived in i)

[2.5 Marks]

- c) i) Define the Noise Equivalent Power (NEP) and the responsivity \mathcal{R} of a photodetector.
 ii) Show that $NEP = \text{rms}(i_n) / \mathcal{R}$
 where i_n is the total noise current in the photodetector.

- iii) Sketch the input optical power (P_s) vs the photocurrent (i_s) characteristic of a photodetector and define the Dynamic Range (DR).

[2.5 Marks]

- d) i) Describe the active region of a p-n junction photodiode.
 ii) Sketch the current - voltage characteristics of a p-n junction photodiode for increasing optical input power.
 iii) Design a circuit to operate the photodiode in the photoconductive (Reverse Bias) region and explain its operation.

[3 Marks]

Q4 a) Explain the difference between a voltage and a power amplifier

[1 Mark]

b) State the differences between Class A, Class B, Class AB and Class C amplifiers.

[2 Marks]

c) State what you understand by the term "negative feedback" in an amplifier?

[1 Mark]

d) A transformer coupled class A audio power amplifier driving an $8\ \Omega$ speaker is shown in Figure Q4 a). The transistor output characteristics are shown in Figure Q4 b). If the circuit component values result in a dc base current of $6\ \text{mA}$ and the input signal V_{in} result in a peak base swing of $4\ \text{mA}$, determine

i) the maximum and the minimum values of V_{ce}

[1 Mark]

ii) the maximum and the minimum values of I_c

[1 Mark]

iii) the rms value of the load current and the load voltage

[1 Mark]

iv) the power dissipated by the transistor

[1 Mark]

v) The efficiency of the amplifier circuit

[2 Marks]

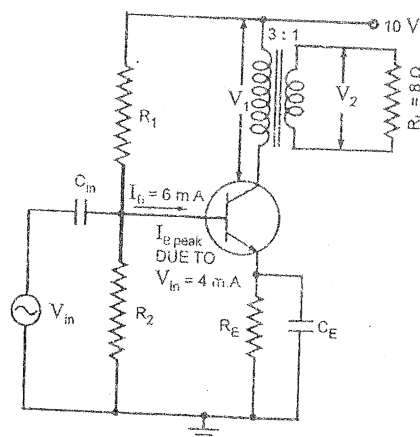


Figure Q4 a)

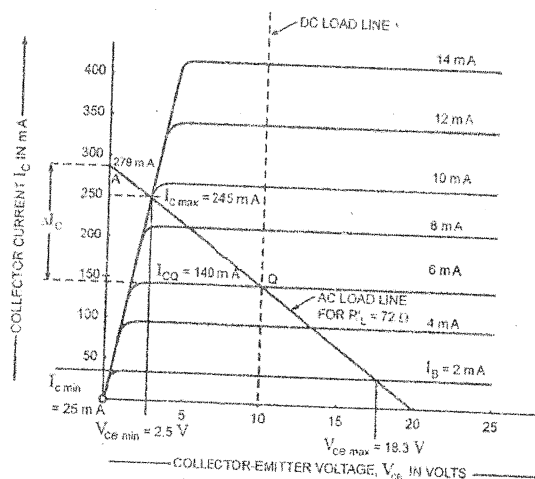


Figure Q4 b)

- Q5 a) Evaluate the acceleration of gravity g , using a simple pendulum. The period of such a pendulum is known to be

$$T = 2\pi\sqrt{l/g}$$

where l is the length of the pendulum.

Measured values are $l = 92.95 \pm 0.1\text{cm}$, $T = 1.936 \pm 0.004\text{s}$

[2 Marks]

- b) Following measurements of the length l and width b of a rectangle were made by a Vernier Caliper.

Table: Vernier Caliper measurements.

$l(\text{mm})$	$b(\text{mm})$
24.25	50.36
24.26	50.35
24.22	50.41
24.28	50.37
24.24	50.36
24.25	50.32
24.22	50.39
24.23	50.38
24.24	50.38
24.22	50.35

The area of the rectangle is defined as $A=l*b$. Considering the standard deviation of the mean (SDOM), estimate the error percentage when you compute the area(A).

[3 Marks]

- c) A student, A, measures the voltage V [Volts] across a resistor 10 times for a constant current and obtains the values

$$V_A = 14.3, 15.4, 15.6, 15.2, 16.1, 16.8, 17.3, 16.5, 15.6, 14.7$$

Independently, another student, B, also measures the voltage V [Volts] across the same resistor 10 times for the same constant current and obtains the values

$$V_B = 13.1, 14.6, 15.3, 14.6, 15.4, 15.8, 16.9, 15.7, 14.4, 16.7$$

Assume that both the measurement sets are normally distributed.

- Whose measurements are more precise? Justify your answer.
- Rewrite both students results in the standard form $x = x_{best} \pm \delta x$ Explain how you calculated the uncertainties.

[5 Marks]